74HC125-Q100; 74HCT125-Q100

Quad buffer/line driver; 3-state

Rev. 1 — 26 February 2013

Product data sheet

1. **General description**

The 74HC125-Q100; 74HCT125-Q100 is a quad buffer/line driver with 3-state outputs controlled by the output enable inputs (nOE). A HIGH on nOE causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes which enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Complies with JEDEC standard no. 7A
- Input levels:
 - ◆ The 74HC125-Q100: CMOS levels
 - ◆ The 74HCT125-Q100: TTL levels
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

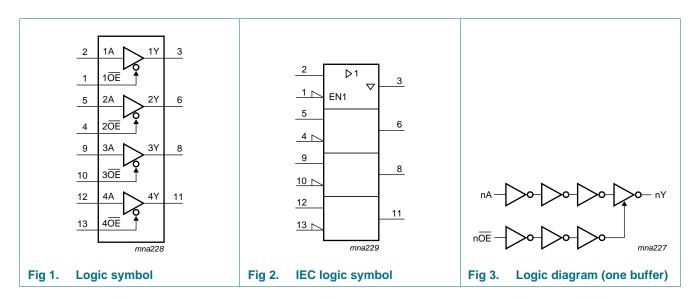
Ordering information 3.

Ordering information Table 1.

Type number	Package						
	Temperature range	Name	Description	Version			
74HC125D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1			
74HCT125D-Q100			3.9 mm				
74HC125PW-Q100	–40 °C to +125 °C	TSSOP14	process and comment of the process o	SOT402-1			
74HCT125PW-Q100	_		body width 4.4 mm				

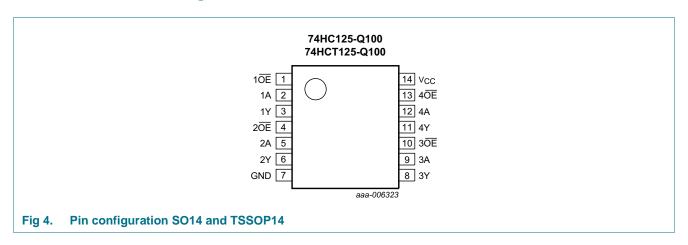


4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1 OE , 2 OE , 3 OE , 4 OE	1, 4, 10, 13	output enable input (active LOW)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Control	Input	Output
nOE	nA	nY
L	L	L
	Н	Н
Н	X	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					•
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	[1] _	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±35	mA
I _{CC}	supply current		-	+70	mA
I _{GND}	ground current		-	-70	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[1] -	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed. For SO14 packages: Ptot derates linearly with 8 mW/K above 70 °C.

For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 $^{\circ}\text{C}.$

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74F	HC125-Q	100	74H	CT125-C	2100	Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_{O}	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
	$V_{CC} = 6.0 \text{ V}$		-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC12	5-Q100			'		'			'	
V_{IH}	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 6.0 \text{ mA}$; $V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	٧
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	-	±5.0	-	±10.0	μА

74HC_HCT125_Q100

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
C _I	input capacitance		-	3.5	-					pF
74HCT1	25-Q100									
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	100	360	-	450	-	490	μΑ
C _I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74HC125-Q1	00									
t _{pd}	propagation	nA to nY; see Figure 5	[1]								
	delay	$V_{CC} = 2.0 \text{ V}$		-	30	100	-	125	-	150	ns
		$V_{CC} = 4.5 \text{ V}$		-	11	20	-	25	-	30	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	9	17	-	21	-	26	ns
t _{en}	enable time	nOE to nY; see Figure 6	[2]								
		$V_{CC} = 2.0 \text{ V}$		-	41	125	-	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}$		-	15	25	-	31	-	38	ns
		$V_{CC} = 6.0 \text{ V}$		-	12	21	-	26	-	32	ns
t _{dis}	disable time	nOE to nY; see Figure 6	[3]								
		$V_{CC} = 2.0 \text{ V}$		-	41	125	-	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}$		-	15	25	-	31	-	38	ns
		$V_{CC} = 6.0 \text{ V}$		-	12	21	-	26	-	32	ns
t _t	transition	nY; see Figure 5	[4]								
	time	$V_{CC} = 2.0 \text{ V}$		-	14	60	-	75	-	90	ns
		$V_{CC} = 4.5 \text{ V}$		-	5	12	-	15	-	18	ns
		$V_{CC} = 6.0 \text{ V}$		-	4	10	-	13	-	15	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC}	<u>[5]</u>	-	22	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		-40 °C 1	to +85 °C	–40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74HCT125-Q	100					1				
t _{pd}	propagation	nA to nY; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 4.5 \text{ V}$		-	15	25	-	31	-	38	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	12	-	-	-	-	-	ns
t _{en}	enable time	nOE to nY; see Figure 6	[2]								
		$V_{CC} = 4.5 \text{ V}$		-	15	28	-	35	-	42	ns
t _{dis}	disable time	nOE to nY; see Figure 6	[3]								
		$V_{CC} = 4.5 \text{ V}$		-	15	25	-	31	-	38	ns
t _t	transition time	nY; see <u>Figure 5</u>	[4]	-	5	12	-	15	-	18	ns
C_{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[5]</u>	-	24	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

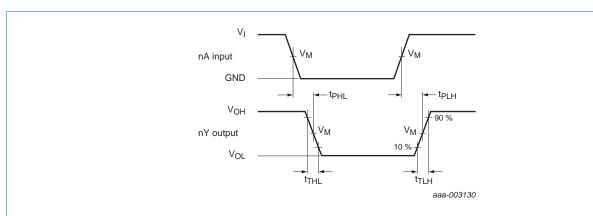
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nA) to output (nY)

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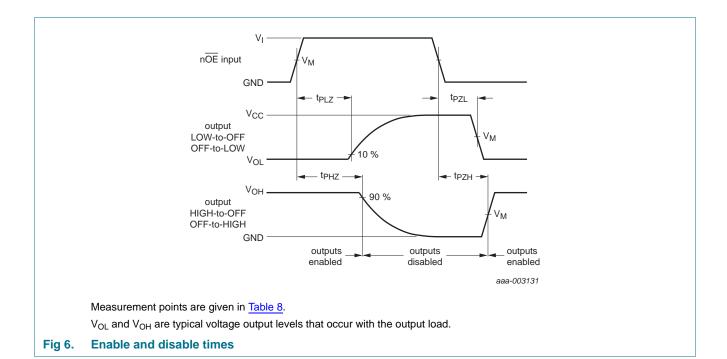
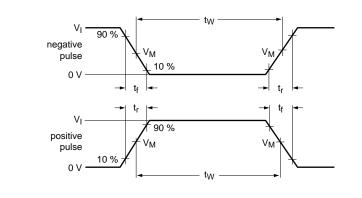
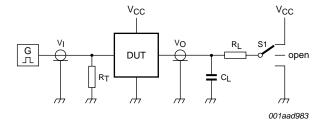


Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74HC125-Q100	0.5V _{CC}	0.5V _{CC}
74HCT125-Q100	1.3 V	1.3 V





Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

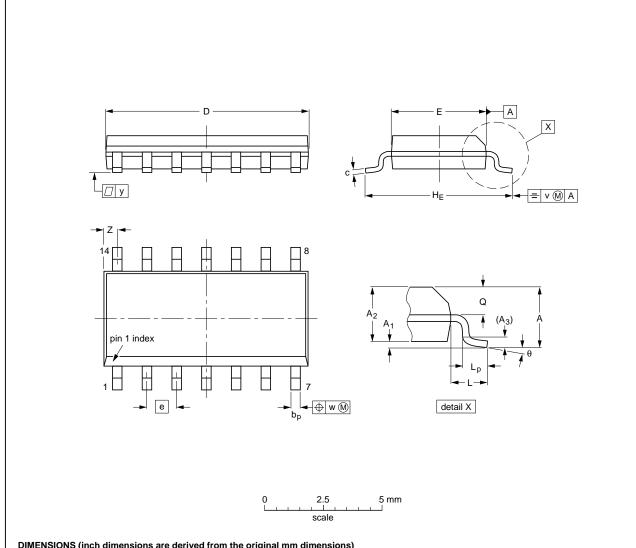
Table 9. Test data

Туре	Input		Load		S1 position				
	VI	t _r , t _f	CL	R_L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
74HC125-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}		
74HCT125-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

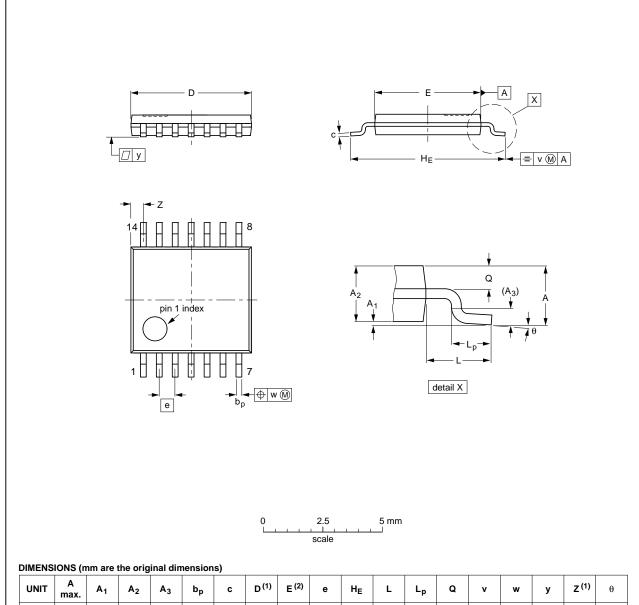
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

Fig 8. Package outline SOT108-1 (SO14)

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



						٠,												
UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

VERSION IEC JEDEC JEITA PROJECTION	DATE	ISSUE DAT	EUROPEAN	RENCES	REFER		OUTLINE			
SOT402.1 MO.153	DATE	ISSUE DAT	PROJECTION	JEITA	JEDEC	IEC	VERSION			
03-1		99-12-27 03-02-18			MO-153		SOT402-1			

Fig 9. Package outline SOT402-1 (TSSOP14)

74HC_HCT125_Q100

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
LSTTL	Low-power Schottky Transistor-Transistor Logic
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
MIL	Military
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT125_Q100 v.1	20130226	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Quad buffer/line driver; 3-state

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